VS-16TTS08FP-M3, VS-16TTS12FP-M3

Vishay Semiconductors

ROHS

High Voltage Phase Control Thyristor, 16 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	10 A			
V _{DRM} /V _{RRM}	800 V, 1200 V			
V _{TM}	1.4 V			
I _{GT}	60 mA			
T _J	-40 °C to 125 °C			
Package	3L TO-220 FullPAK			
Circuit configuration	Single SCR			

FEATURES





• 125 °C max. operating junction temperature

Material categorization: for definitions of FREE compliance please see www.vishav.com/doc?99912

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А				

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	10	^			
I _{RMS}		16	A			
V _{DRM} /V _{RRM}		800, 1200	V			
I _{TSM}		200	A			
V _T	10 A, T _J = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
T,I	Range	-40 to 125	°C			

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
VS-16TTS08FP-M3	800	800	10				
VS-16TTS12FP-M3	1200	1200	10				

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES		UNITS
PARAMETER	STIVIBUL		TEST CONDITIONS		MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 70 °C, 18	30° conduction, half sine wave	1	0	
Maximum RMS on-state current	I _{RMS}				6	Α
Maximum peak, one-cycle,	I	10 ms sine pu	lse, rated V _{RRM} applied	1	70	A
non-repetitive surge current	I _{TSM}	10 ms sine pu	lse, no voltage reapplied	2	00	
Maximum I ² t for fusing	l ² t	10 ms sine pu	lse, rated V _{RRM} applied	1-	44	A ² s
Maximum 1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		A-S
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 m	ns, no voltage reapplied	20	000	A²√s
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °C		1	.4	٧
On-state slope resistance	r _t	T _J = 125 °C		24	1.0	mΩ
Threshold voltage	V _{T(TO)}	1j=125 C		1	.1	V
Maximum rayaraa and direct lookage current	1 /1	T _J = 25 °C	V - Peted V A/	0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$V_R = Rated V_{RRM}/V_{DRM}$		1	0]
Holding current	l _H	Anode supply = 6 V, resistive load, initial I_T = 1 A 16TTS08FP, 16TTS12FP, T_J = 25 °C		150	mA	
Maximum latching current	IL	Anode supply = 6 V, resistive load, T _J = 25 °C		2	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ 500		00	V/µs	
Maximum rate of rise of turned-on current	dI/dt	150		A/µs		

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P_{GM}		8.0	w	
Maximum average gate power	P _{G(AV)}		2.0] "	
Maximum peak positive gate current	+ I _{GM}		1.5	Α	
Maximum peak negative gate voltage	- V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, T _J = -10 °C	90	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	60		
		Anode supply = 6 V, resistive load, T _J = 125 °C	35		
		Anode supply = 6 V, resistive load, T _J = -10 °C	3.0		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V	
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0]	
Maximum DC gate voltage not to trigger	V_{GD}	$T_{J} = 125 ^{\circ}\text{C}, V_{DRM} = \text{Rated value} \qquad \qquad \qquad \qquad 0.25$			
Maximum DC gate current not to trigger	I_{GD}			mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9			
Typical reverse recovery time	t _{rr}	T. = 195 °C	4	μs		
Typical turn-off time	tq	T _J = 125 °C	110			



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
			Case style 3L TO-220 FullPAK	16TTS	08FP
Marking device		16TTS		12FP	

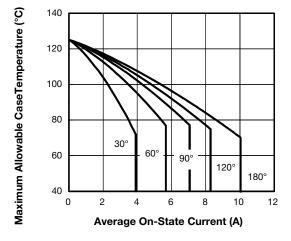


Fig. 1 - Current Rating Characteristics

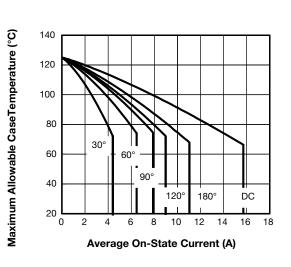


Fig. 2 - Current Rating Characteristics

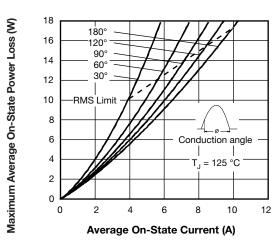


Fig. 3 - On-State Power Loss Characteristics

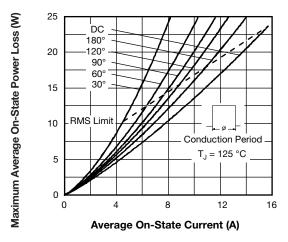
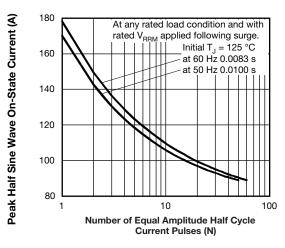


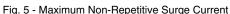
Fig. 4 - On-State Power Loss Characteristics



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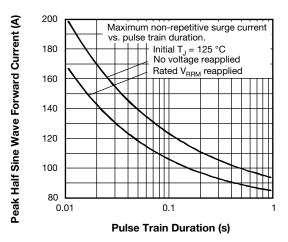


Fig. 6 - Maximum Non-Repetitive Surge Current

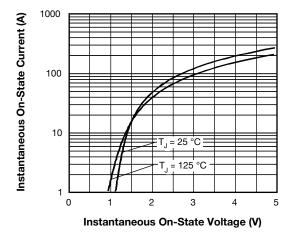


Fig. 7 - On-State Voltage Drop Characteristics

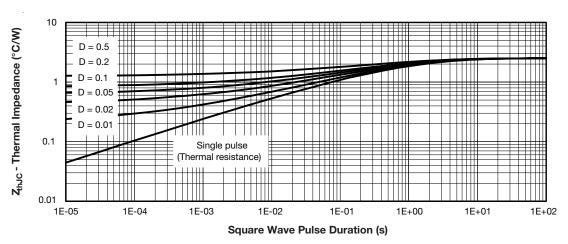


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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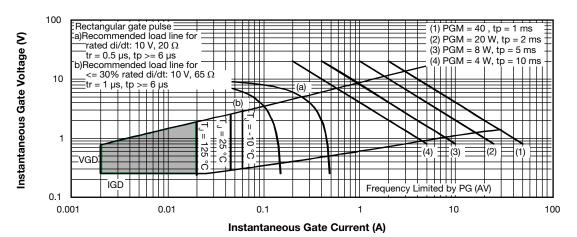


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	16	т	Т	s	12	FP	-М3
	1	2	3	4	5	6	7	8
	Vishay Semiconductors productCurrent rating, RMS value							

3 - Circuit configuration:

T = single thyristor

- Package:

T = TO-220AB

5 - Type of silicon: S = converter grade

6 - Voltage code x 100 = V_{RRM} - 08 = 800 V 12 = 1200 V

7 - FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes				
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes				

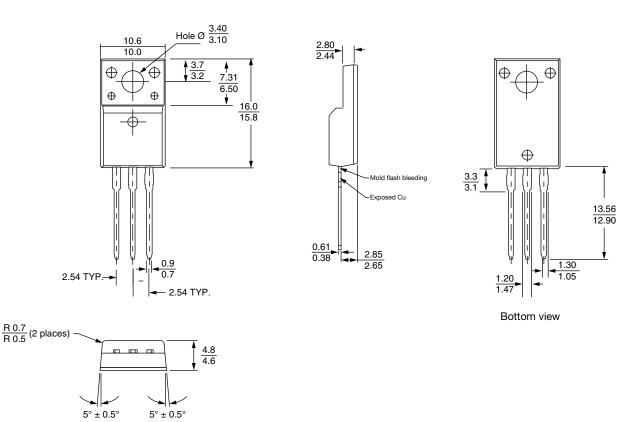
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?96155		
Part marking information	www.vishay.com/doc?95456		



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3L TO-220 FullPAK

DIMENSIONS in millimeters



Notes

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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